

Silicon Super Fast Recovery Diode

$V_{RRM} = 50\text{ V} - 600\text{ V}$

$I_F = 100\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

D-67 Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

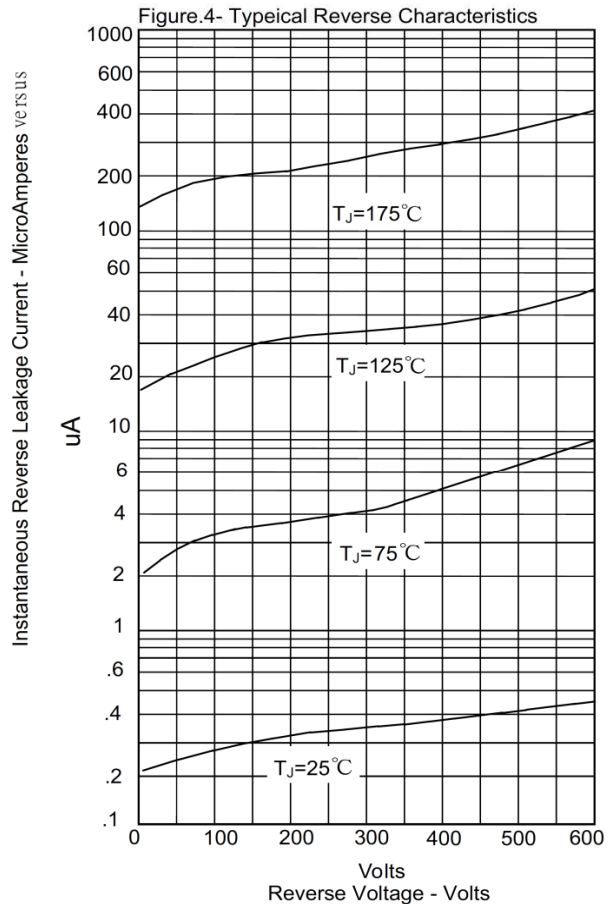
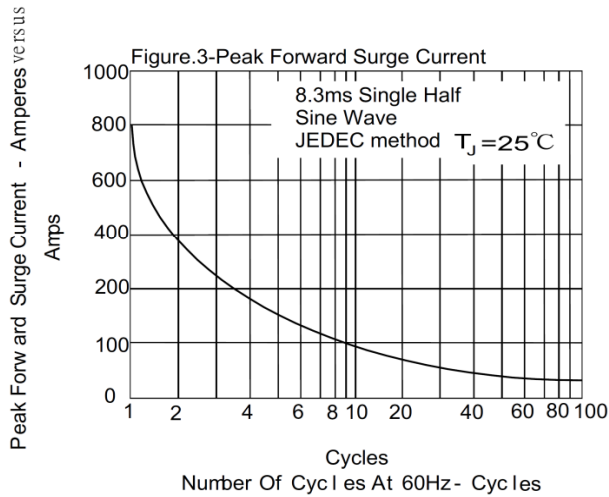
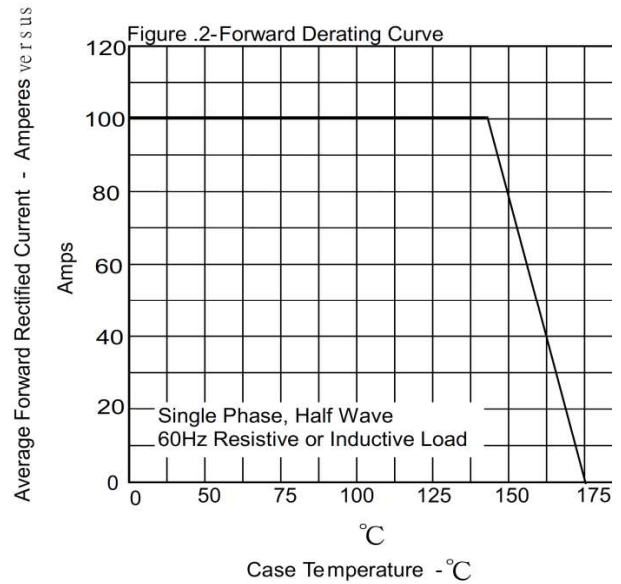
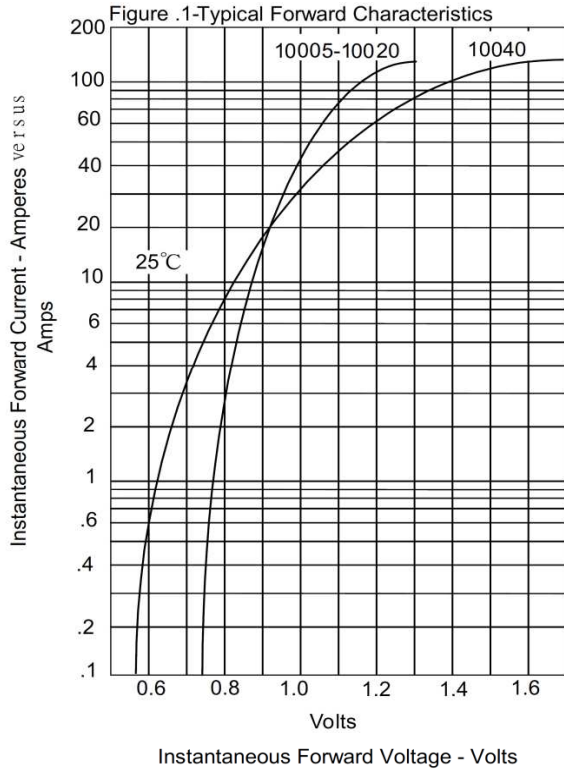
Parameter	Symbol	Conditions	MURH10040 (R)	MURH10060 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		400	600	V
RMS reverse voltage	V_{RMS}		280	420	V
DC blocking voltage	V_{DC}		400	600	V
Continuous forward current	I_F	$T_C \leq 140\text{ °C}$	100	100	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	800	800	A
Operating temperature	T_j		-65 to 175	-65 to 175	°C
Storage temperature	T_{stg}		-65 to 175	-65 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MURH10040 (R)	MURH10060 (R)	Unit
Diode forward voltage	V_F	$I_F = 100\text{ A}$, $T_j = 25\text{ °C}$	1.3	1.7	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ °C}$	25	25	μA
		$V_R = 50\text{ V}$, $T_j = 125\text{ °C}$	1	1	mA

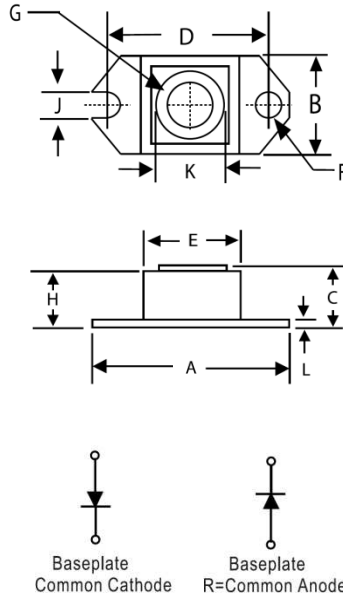
Recovery Time

Maximum reverse recovery time	T_{RR}	$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{RR} = 0.25\text{ A}$	90	110	nS
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Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	1.515	1.560	38.48	39.62	
B	.725	.775	18.42	19.69	
C	.595	.625	15.11	15.88	
D	1.182	1.192	30.02	30.28	
E	.736	.744	18.70	18.90	
F	.152	.160	3.86	4.061	∅
G	1/4- 20 UNC				
H	.540	.580	13.72	14.73	
J	.156	.160	3.96	4.06	
K	.480	.492	12.20	12.50	∅
L	.120	.130	3.05	3.30	